

PATENT

Atty. Dkt. No. AMAT/5619/DSM/LOW K/JW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Nguyen, et al.

Serial No.: 09/912,103

Confirmation No.: 4476

Filed: July 23, 2001

For: Selective Etching of
Organosilicate Films Over
Silicon Oxide Stop Etch Layers

Group Art Unit: 2823

Examiner: Khiem D. Nguyen

BOX AF
Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF FACSIMILE
TRANSMISSION UNDER 37 CFR 1.8

I hereby certify that this correspondence and the documents referred to as attached therein are being facsimile transmitted to the U.S. Patent and Trademark Office to the fax number indicated by the Examiner, namely, fax number 703-746-9179 to the attention of the named Examiner, on the date below.

4/14/03

Date

Keith R. Moser

Signature

RESPONSE TO FINAL OFFICE ACTION DATED FEBRUARY 14, 2003

In response to the Final Office Action dated February 14, 2003, having a shortened statutory period for response set to expire on May 14, 2003, please enter this response and reconsider the claims pending in the application for reasons discussed below. Although Applicant believes that no fee is due in conjunction with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/AMAT/5619/KMT, for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

THE PENDING CLAIMS:

1. A method of fabricating a damascene structure, comprising:
- (a) forming a barrier layer on a substrate having a metal layer thereon;

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